

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a multilayer structure is disclosed, which comprises at least two wiring layers, and a via contact formed between the at 5 least two layers and made of the same metal wiring material as the metal wiring material of the at least two wiring layers, wherein the metal wiring material of the via contact contains an additive which is not contained in the metal wiring materials of the at least 10 two wiring layers.